

# MSKSEMI 美森科

SEMICONDUCTOR



ESD



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## NTTFS5826NL-MS

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Product specification

## Description

The NTTFS5826NL-MS uses advanced trench technology to provide excellent  $R_{DS(ON)}$ , low gate charge and operation with gate voltages as low as 4.5V. This device is suitable for use as a Battery protection or in other Switching application.

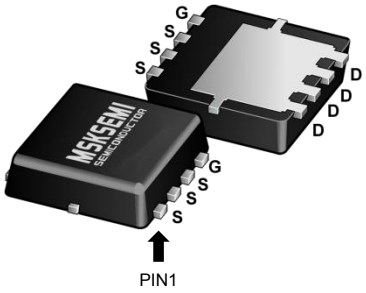
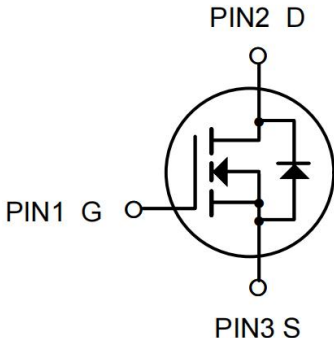

## Features

- $V_{DS} = 60V$   $I_D = 20A$
- $R_{DS(ON)} < 40m\Omega$  @  $V_{GS}=10V$

## Application

- Battery protection
- Load switch
- Uninterruptible power supply

## Reference News

PACKAGE OUTLINE	N-Channel MOSFET	Marking
 <p>DFN3X3-8L</p>		

## Absolute Maximum Ratings (TC=25°C unless otherwise noted)

Symbol	Parameter	Rating	Units
$V_{DS}$	Drain-Source Voltage	60	V
$V_{GS}$	Gate-Source Voltage	$\pm 20$	V
$I_D @ T_A=25^\circ C$	Continuous Drain Current, $V_{GS}$ @ 10V <sup>1</sup>	20	A
$I_D @ T_A=70^\circ C$	Continuous Drain Current, $V_{GS}$ @ 10V <sup>1</sup>	10	A
$I_{DM}$	Pulsed Drain Current <sup>2</sup>	46	A
EAS	Single Pulse Avalanche Energy <sup>3</sup>	25.5	mJ
$I_{AS}$	Avalanche Current	20	A
$P_D @ T_C=25^\circ C$	Total Power Dissipation <sup>4</sup>	34.7	W
$T_{STG}$	Storage Temperature Range	-55 to 175	°C
$T_J$	Operating Junction Temperature Range	-55 to 175	°C
$R_{\theta JA}$	Thermal Resistance Junction-Ambient <sup>1</sup>	62	°C/W

**AElectrical Characteristics** ( $T_J=25^\circ\text{C}$  unless otherwise specified)

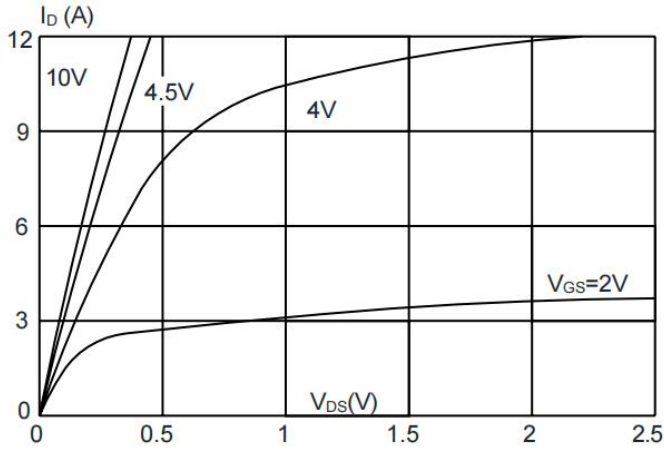
Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
<b>Off Characteristic</b>						
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=250\mu A$	60	-	-	V
$I_{DSS}$	Zero Gate Voltage Drain Current	$V_{DS}=60V, V_{GS} = 0V,$	-	-	1.0	$\mu A$
$I_{GSS}$	Gate to Body Leakage Current	$V_{DS}=0V, V_{GS} = \pm 20V$	-	-	$\pm 100$	$\mu A$
<b>On Characteristics</b>						
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}, I_D=250\mu A$	1.0	1.6	2.5	V
$R_{DS(on)}$	Static Drain-Source on-Resistance <small>note3</small>	$V_{GS}=10V, I_D=5A$	-	31	40	m $\Omega$
		$V_{GS}=4.5V, I_D=3A$	-	36	50	
<b>Dynamic Characteristics</b>						
$C_{iss}$	Input Capacitance	$V_{DS}=25V, V_{GS}=0V,$ $f=1.0MHz$	-	1148	-	pF
$C_{oss}$	Output Capacitance		-	58.5	-	pF
$C_{rSS}$	Reverse Transfer Capacitance		-	49.4	-	pF
$Q_g$	Total Gate Charge	$V_{DS}=30V, I_D=2.5A,$ $V_{GS}=10V$	-	20.3	-	nC
$Q_{gs}$	Gate-Source Charge		-	3.7	-	nC
$Q_{gd}$	Gate-Drain("Miller") Charge		-	5.3	-	nC
<b>Switching Characteristics</b>						
$t_{d(on)}$	Turn-on Delay Time	$V_{DS}=30V, I_D=5A,$ $R_G=1.8\Omega, V_{GS}=10V$	-	7.6	-	ns
$t_r$	Turn-on Rise Time		-	20	-	ns
$t_{d(off)}$	Turn-off Delay Time		-	15	-	ns
$t_f$	Turn-off Fall Time		-	24	-	ns
<b>Drain-Source Diode Characteristics and Maximum Ratings</b>						
$I_S$	Maximum Continuous Drain to Source Diode Forward Current		-	-	5	A
$I_{SM}$	Maximum Pulsed Drain to Source Diode Forward Current		-	-	20	A
$V_{SD}$	Drain to Source Diode Forward Voltage	$V_{GS}=0V, I_S=5A$	-	-	1.2	V
$t_{rr}$	Body Diode Reverse Recovery Time	$I_F=5A, di/dt=100A/\mu s$	-	29	-	ns
$Q_{rr}$	Body Diode Reverse Recovery Charge		-	43	-	nC

Notes:1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature

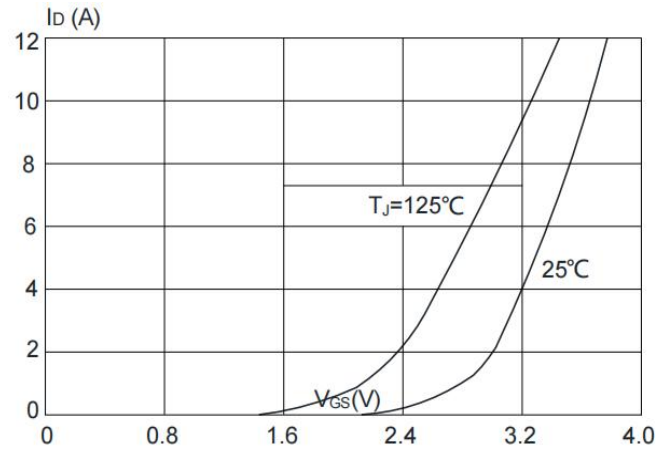
 2. EAS condition :  $T_J=25^\circ\text{C}, V_{DD}=30V, V_G=10V, L=0.5mH, R_g=25\Omega, I_{AS}=8.7A$ 

 3. Pulse Test: Pulse Width $\leq 300\mu s$ , Duty Cycle $\leq 0.5\%$

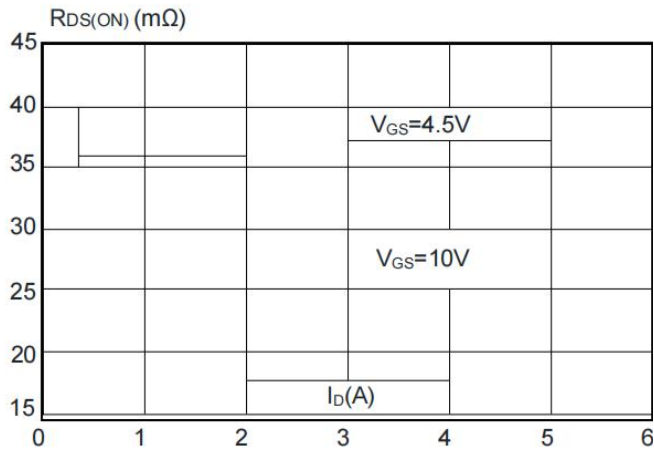
**Typical Performance Characteristics**



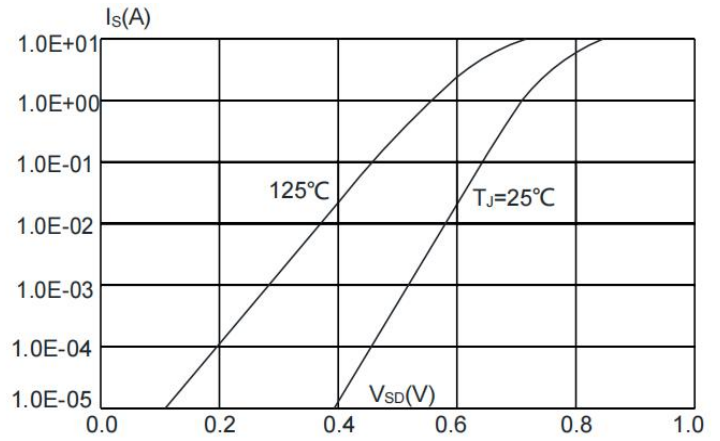
**Figure 1:** Output Characteristics



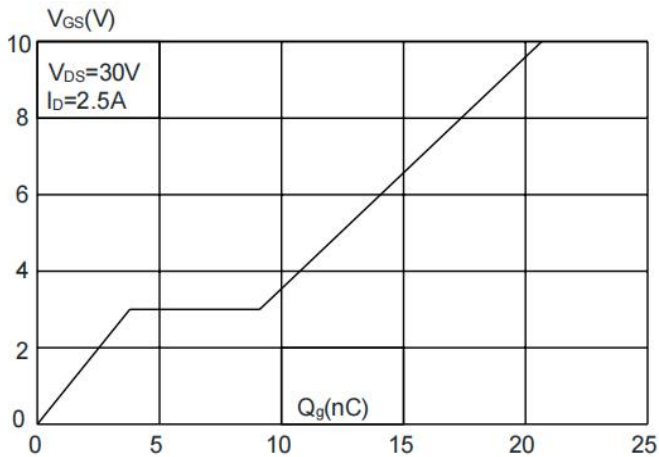
**Figure 2:** Typical Transfer Characteristics



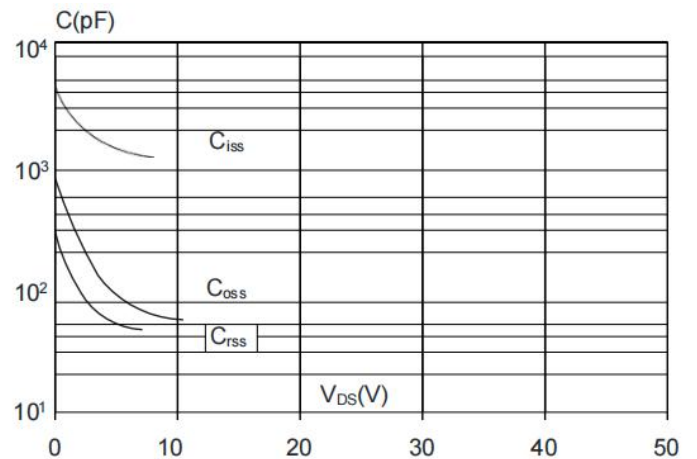
**Figure 3:** On-resistance vs. Drain Current



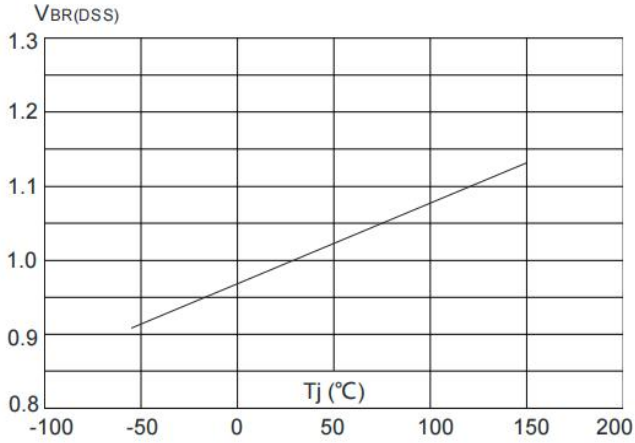
**Figure 4:** Body Diode Characteristics



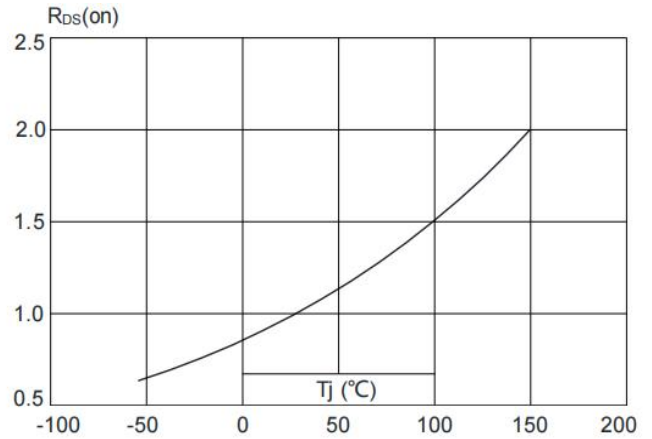
**Figure 5:** Gate Charge Characteristics



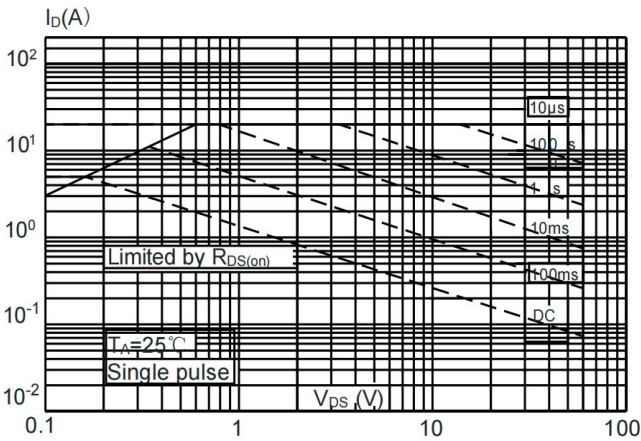
**Figure 6:** Capacitance Characteristics



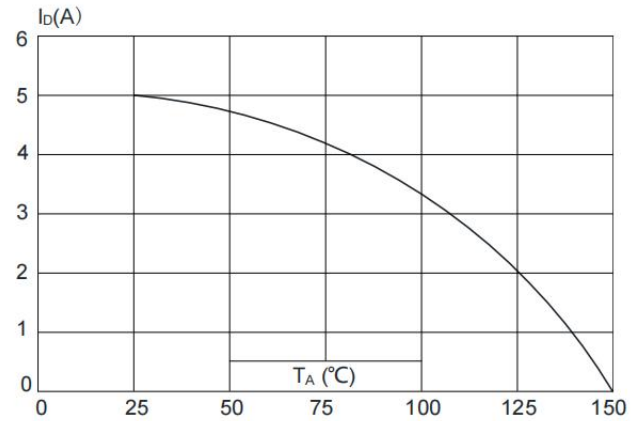
**Figure 7:** Normalized Breakdown Voltage vs. Junction Temperature



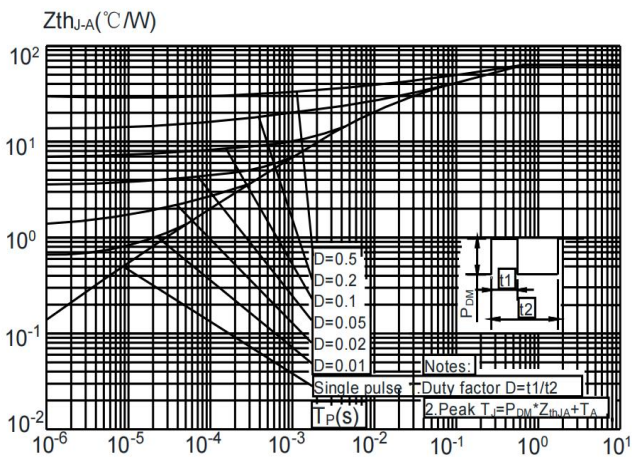
**Figure 8:** Normalized on Resistance vs. Junction Temperature



**Figure 9:** Maximum Safe Operating Area

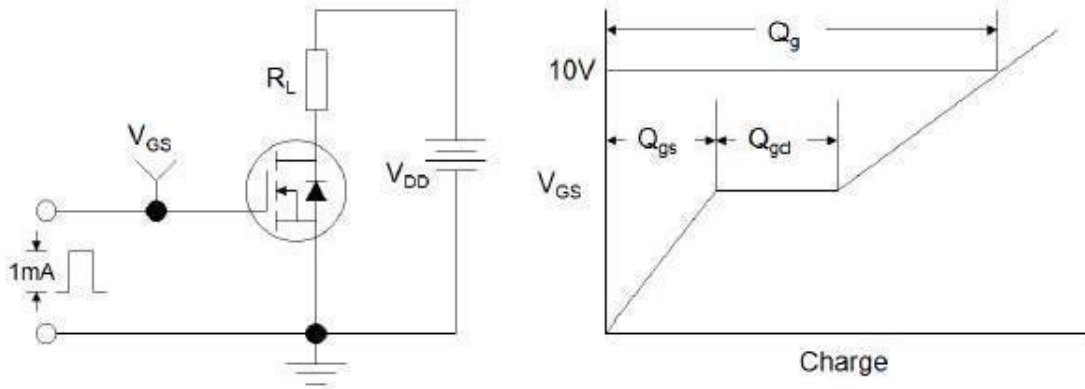


**Figure 10:** Maximum Continuous Drain Current vs. Ambient Temperature

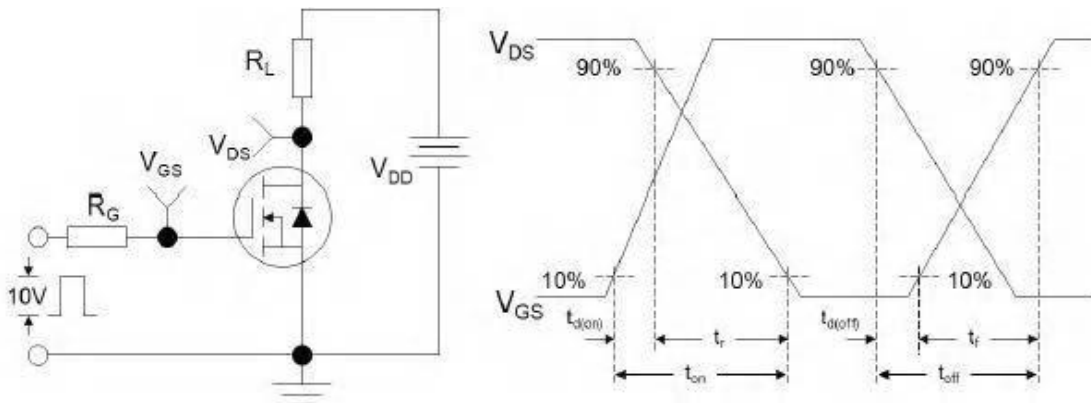


**Figure.11:** Maximum Effective Transient Thermal Impedance, Junction-to-Ambient

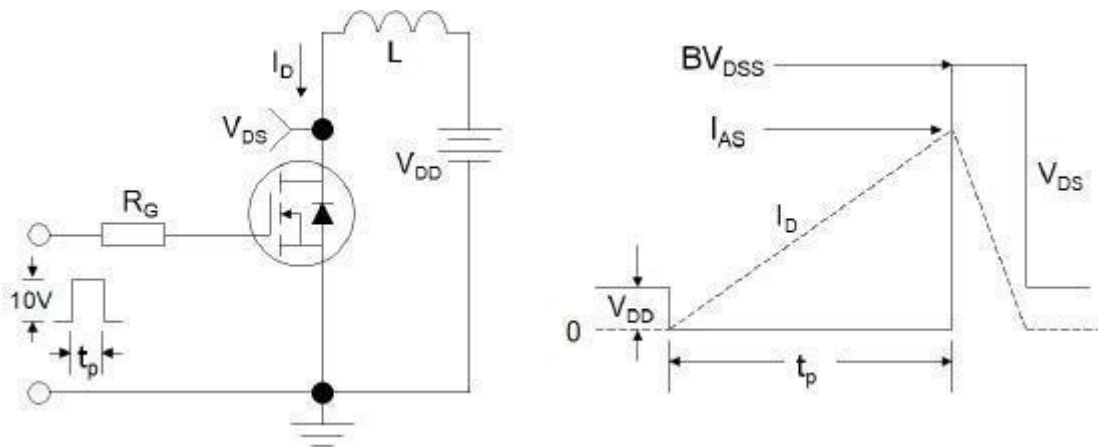
**Test Circuit**



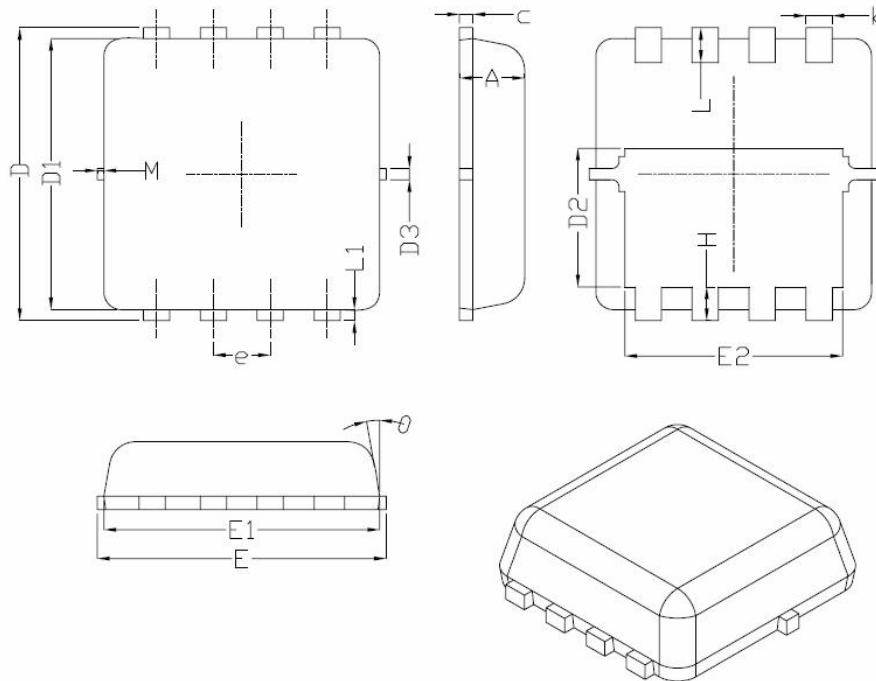
**Figure 1: Gate Charge Test Circuit & Waveform**



**Figure 2: Resistive Switching Test Circuit & Waveforms**



**Figure 3: Unclamped Inductive Switching Test Circuit & Waveforms**

**DFN3X3-8L Package Information**


Symbol	Dimensions In Millimeters		
	Min.	Nom.	Max.
A	0.70	0.75	0.80
b	0.25	0.30	0.35
c	0.10	0.15	0.25
D	3.25	3.35	3.45
D1	3.00	3.10	3.20
D2	1.48	1.58	1.68
D3	-	0.13	-
E	3.20	3.30	3.40
E1	3.00	3.15	3.20
E2	2.39	2.49	2.59
e	0.65BSC		
H	0.30	0.39	0.50
L	0.30	0.40	0.50
L1	-	0.13	-
M	*	*	0.15
θ		10°	12°

**REEL SPECIFICATION**

P/N	PKG	QTY
NTTFS5826NL-MS	DFN3X3-8L	5000

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